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PPLICATION NO.	FILING DA	TE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/594,510	06/16/20	00	Alan G. Wood	M4065.0184/P184	4065.0184/P184 2407	
24998	7590 0-	4/27/2004		EXAM	INER	
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP				LUU, CHUONG A		
2101 L STRE WASHINGT	EET NW ON, DC 2003	7-1526		ART UNIT	ART UNIT PAPER NUMBER	
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DATE MAILED: 04/27/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No. Applicant(s)		
Office Action Summers	09/594,510 WOOD ET AL.		
Office Action Summary	Examiner	Art Unit	ليه
	Chuong A Luu	2825	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	correspondence ad	ldress
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period we Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day vill apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed is will be considered timel the mailing date of this o D (35 U.S.C. § 133).	y. ommunication.
Status			
1) Responsive to communication(s) filed on Febru	uary 04, 2004.		
	action is non-final.		
3) Since this application is in condition for allowar closed in accordance with the practice under E			e merits is
Disposition of Claims			
4) Claim(s) 1-23 and 35-40 is/are pending in the a 4a) Of the above claim(s) is/are withdraw 5) Claim(s) 19-23 is/are allowed. 6) Claim(s) 1-18 and 35-40 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or	vn from consideration.		
Application Papers			
9) The specification is objected to by the Examine	r.		
10) The drawing(s) filed on is/are: a) acce			
Applicant may not request that any objection to the			
Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Expression 11.			• •
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau	s have been received. s have been received in Applicati ity documents have been receive (PCT Rule 17.2(a)).	on No ed in this National	Stage
* See the attached detailed Office action for a list of	of the certified copies not receive	d.	
Attachment(s)	_		
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Summary Paper No(s)/Mail Da		
Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	5) Notice of Informal P 6) Other:)-152)

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DETAILED ACTION

Request For Continued Examination (RCE)

The request filed on February 4, 2004 for a Request For Continued Examination (RCE) under 37 CFR 1.53(d) based on parent Application No. 09/594,510 is acceptable and a RCE has been established. An action on the RCEA follows.

PRIOR ART REJECTIONS

Statutory Basis

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claim Rejections - 35 USC § 103

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The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

The Rejections

Claims 1-3, 5-8, 10-16 and 18 are rejected under 35 U.S.C. 102(e) as being anticipated by Corisis (U.S. 6,163,956).

Corisis discloses a method of making chip scale package with

(1) forming conductive structures (46) in contact with a top surface of a dielectric subtrate;

subsequently, forming a layered assembly by attaching a wafer to said dielectric substrate (see Figure 5);

forming input/output devices in contact with said conductive traces (see Figure 5);

testing semiconductor devices in said wafer (see column 4, lines 60-62); subsequently, dicing said layered assembly (see column 4, lines 40-41);

- (2) further comprising the step of connecting said semiconductor devices to input/output devices (see column 4, lines 35-39. Figure 5);
- (3) wherein said testing is conducted through said input/output devices (see Figure 5)
- (5) wherein said step of forming said layered assembly includes the step of adhering said wafer to said dielectric substrate (see Figure 5);

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(6) further comprising the step of electrically connecting said semiconductor devices to ball grid arrays on said dielectric substrate (see Figure 5);

- (8) wherein said connecting step comprises the step of connecting solder bumps on said wafer to circuit traces on said dielectric substrate (see column 4, lines 1-5. Figure 5);
- (10) further comprising the step of providing an electrode pad (15) in said layered assembly (see Figure 5);
 - (11) providing conductive structures in contact with a top surface of a dielectric substrate (see Figure 5);

subsequently, forming a layered assembly by attaching a wafer and a stiff metal layer to said dielectric substrate (see Figure 5);

placing ball grid arrays in contact with said conductive structures;

connecting semiconductor devices in said semiconductor wafer to said ball grid arrays (see Figure 5);

subsequently, dicing said layered assembly (see column 4, lines 40-41);

- (12) wherein said forming step comprises the step of adhering said wafer to said metal layer (see Figure 5);
- (7); (13); (14) wherein said connecting step comprises the step of locating wire bonds in openings through said dielectric substrate (see Figure 5);
- (15) wherein said connecting step comprises the step of connecting solder bumps on said wafer to conductive traces on said dielectric substrate (see Figure 5);

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(16) further comprising the step of connecting said traces to conductive vias extending through said dielectric substrate (see Figure 5).

(18) further comprising the step of testing said semiconductor devices through said ball grid arrays (see column 1, line 65).

Claims 9 and 17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Corisis (U.S. 6,163,956) in view of Takahashi et al. (U.S. 6,153,448).

Corisis teaches everything above except for wherein said dicing step is performed by a saw. However, Takahashi discloses a method of forming a semiconductor device with (9); (17) wherein said dicing step is performed by a saw (see column 8, line 63). It would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the teachings above to separate the semiconductor device into individual component by using a saw during fabrication a semiconductor structure.

Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Corisis (U.S. 6,163,956) in view of Smith (US 6,064,217).

Corisis teaches everything above except for further comprising the step of discarding one or more defective packages. However, Smith discloses a reusable test socket with (4) further comprising the step of discarding one or more defective packages (see column 12, lines 2-13). It would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the teachings

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above to conduct to determine whether the chips are good or bad before further completion the fabrication a semiconductor device.

Claims 35 and 37 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lam (U.S. 6,344,401 B1) in view of Kobayashi et al. (U.S. 4,781,969)

Lam discloses a method of forming a stacked-die integrated circuit chip package on a wafer level with

(35) connecting said semiconductor devices to respective ball grid arrays (50) located on said substrate (see Figures 6-8);

testing said semiconductor devices through said ball grid arrays (see column 4, lines 16-34);

(37) further comprising the step of singulating packages from said wafer and said substrate (see column 4, lines 1-57).

Lam teaches everything above except for using a flexible substrateg packages. However, Kobayashi discloses a printed circuit board with (35)...... adhering said wafer to a flexible substrate (see column 1, lines 38-43). It would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the teachings of Lam and Kobayashi by using a flexible substrate for fabricating a semiconductor device to exceed its performance criteria.

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Claims 36 and 38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lam (U.S. 6,344,401 B1) in view of Kobayashi et al. (U.S. 4,781,969), and further view of Lam (5,137,836)

Lam and Kobayashi diclose everything above except for identifying defective packages. Furthermore, Lam discloses a method of manufacturing a repairable multichip module by (36); (38) further comprising the step of segregating defective packages from other packages (see column 3, lines 1-60). It would have been obvious to one having ordinary skill in the art at the time the invention was made to combine the teachings above to identifying one or more defective chip during fabrication of a semiconductor device.

Allowable Subject Matter

Claims 19-23 are allowed.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Chuong A Luu whose telephone number is (571) 272-1902. The examiner can normally be reached on M-F (6:30-3:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on (571) 272-1907. The fax phone numbers

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for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (571) 272-1975.

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April 8, 2004